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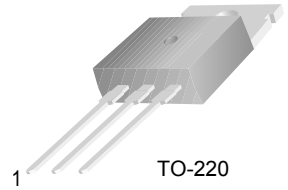
SEMICONDUCTOR®

FJP3307D

High Voltage Fast Switching NPN Power Transistor

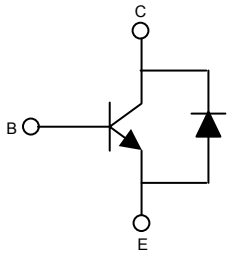
Features

- Built-in Diode between Collector and Emitter
- Suitable for Electronic Ballast and Switch Mode Power Supplies



TO-220
1.Base 2.Collector 3.Emitter

Internal Schematic Diagram



Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	8	A
I_{CP}	* Collector Current (Pulse)	16	A
I_B	Base Current (DC)	4	A
P_C	Collector Dissipation (T_C = 25°C)	80	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-55 ~ 150	°C

* Pulse Test: PW = 300μs, Duty Cycle = 2% Pulsed

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 500μA, I_E = 0	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5mA, I_B = 0	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 500μA, I_C = 0	9			V
I_{EBO}	Emitter Cut-off Current	V_{EB} = 9V, I_C = 0			1	mA
h_{FE1} h_{FE2}	DC Current Gain	V_{CE} = 5V, I_C = 2A V_{CE} = 5V, I_C = 5A	8 5		40 30	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 2A, I_B = 0.4A			1	V
		I_C = 5A, I_B = 1A			2	V
		I_C = 8A, I_B = 2A			3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 2A, I_B = 0.4A			1.2	V
		I_C = 5A, I_B = 1A			1.6	V

Electrical Characteristics T_C = 25°C unless otherwise noted (Continued)

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
V_F	Diode Forward Voltage	I_C = 3A			2.5	V
C_{ob}	Output Capatitance	V_{CB} = 10V, I_E = 0, f = 1MHz		60		pF
t_{STG}	Storage Time	V_{CC} = 125V, I_C = 5A I_{B1} = -I_{B2} = 1A, R_L = 50Ω			3	μs
t_F	Fall Time				0.7	μs
t_{STG}	Storage Time	V_{CC} = 30V, I_C = 5A, L=200μH I_{B1}=1A, R_{BB} = 0Ω, $V_{BE(OFF)}$= -5V V_{CLAMP} = 250V			2.3	μs
t_F	Fall Time				150	ns

* Pulse test: PW=300μs, Duty cycle=2%

h_{FE} Classification

Classification	H1	H2
h_{FE1}	15 ~ 28	26 ~ 39

Typical Performance Characteristics

Figure 1. Static Characterstic

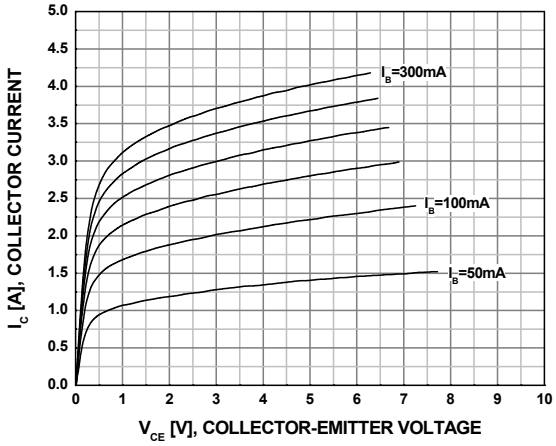


Figure 2. DC Current Gain (H1 Grade)

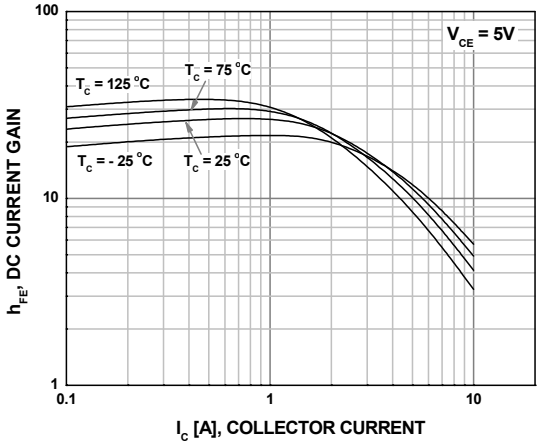


Figure 3. DC Current Gain (H2 Grade)

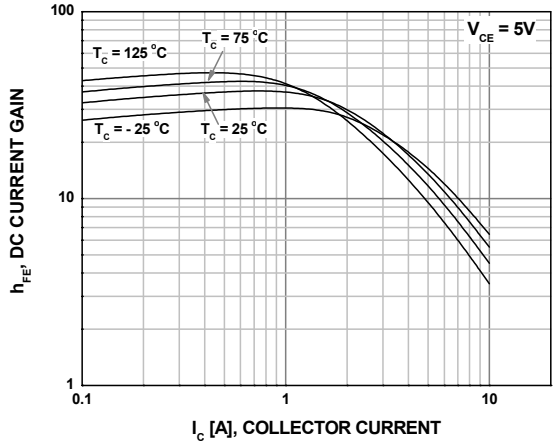


Figure 4. Collector-Emitter Saturation Voltage

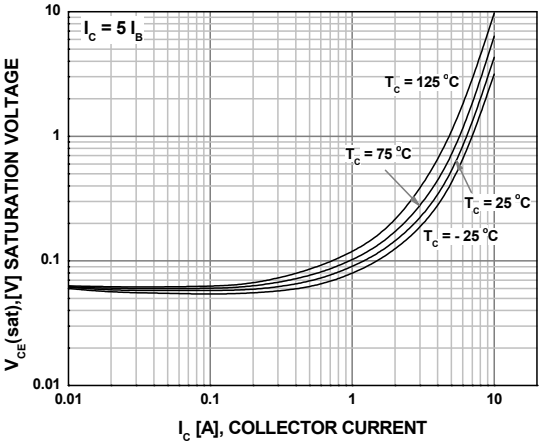


Figure 5. Base-Emitter Saturation Voltage

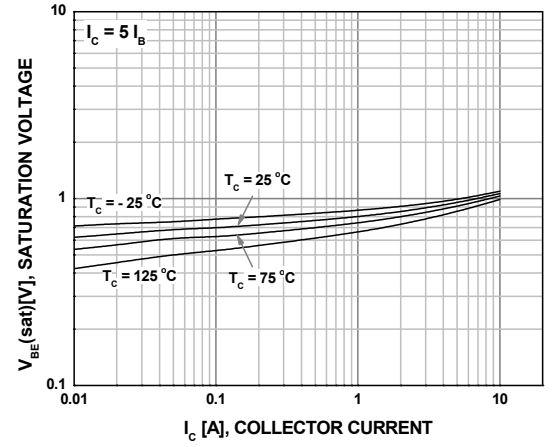
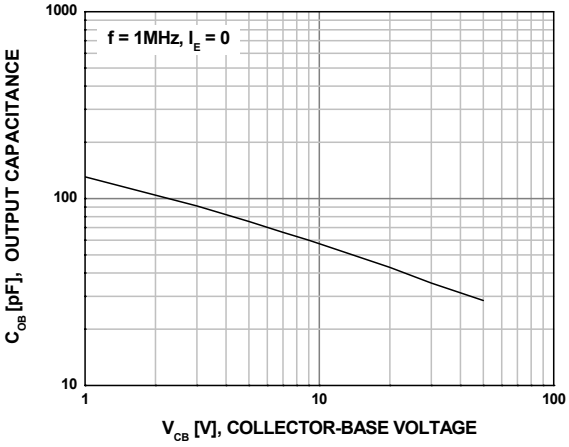


Figure 6. Output Capacitance



Typical Performance Characteristics (Continued)

Figure 7. Power Derating

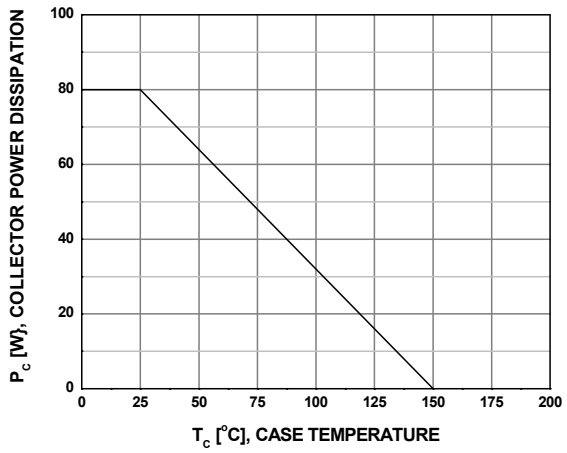


Figure 8. Reverse Biased Safe Operating Area

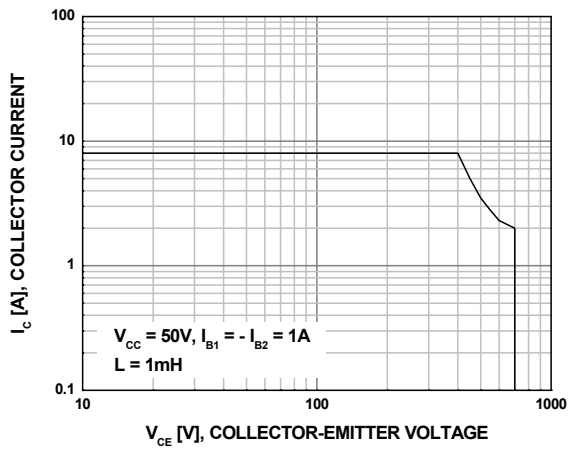
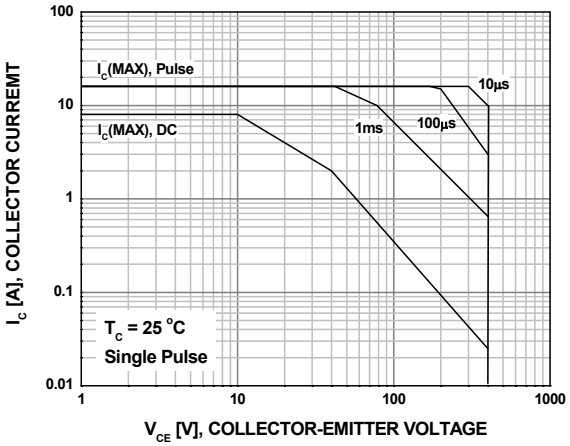
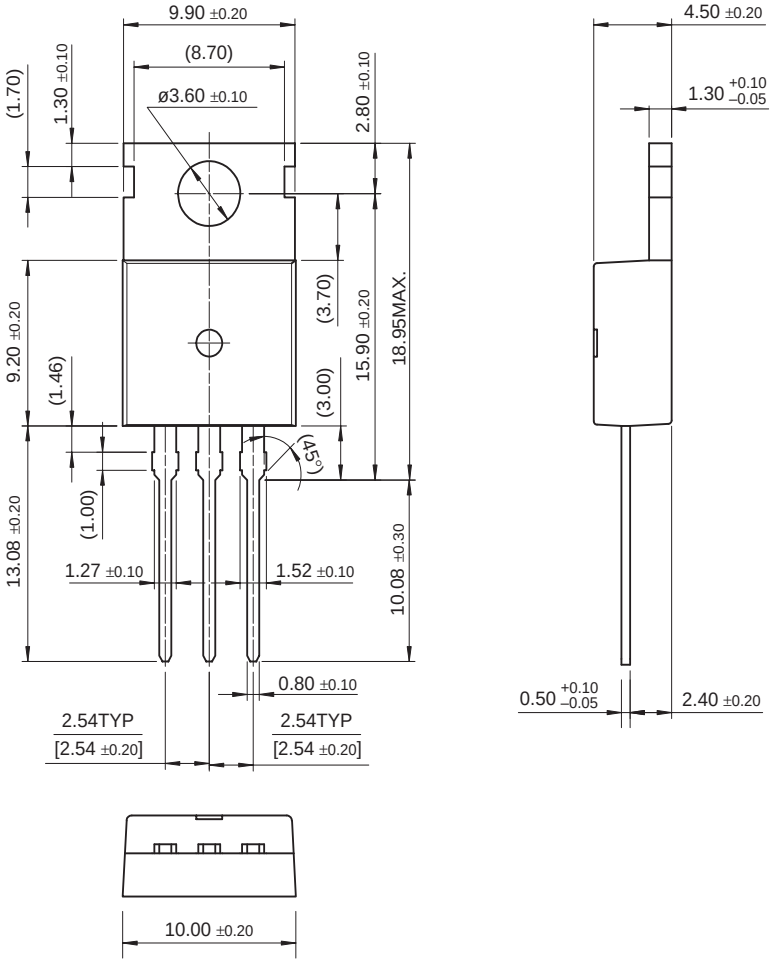


Figure 9. Forward Biased Safe Operating Area



Mechanical Dimensions

TO-220



Dimensions in Millimeters

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